

Appl. No. 09/938,260  
Reply to Office action of 09/15/2003

**Amendments to th Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

Claims 1-27(cancelled).

Claim 28 (currently amended) An integrated circuit structure, comprising:

at least two metal interconnect lines;

a liner comprising ~~silicon and carbon~~ silicon boron-carbide located on and between said metal interconnect lines; and

a dielectric layer positioned between said metal interconnect lines, the liner positioned between at least a portion of the dielectric layer and the metal interconnect lines.

Claim 29 (canceled)

Claim 30 (previously presented): The integrated circuit structure of Claim 28, wherein the dielectric layer comprises an intralevel dielectric layer positioned between metal interconnect lines in a level of the integrated circuit structure.

Claim 31 (previously presented): The integrated circuit structure of Claim 28, wherein the dielectric layer comprises an interlevel dielectric layer positioned between conductive elements in different levels of the integrated circuit structure.

Claim 32 (previously presented): The integrated circuit structure of Claim 28, wherein the dielectric layer comprises a fluorinated dielectric material.

Claim 33 (previously presented): The integrated circuit structure of Claim 28, wherein the dielectric layer comprises polytetrafluoroethylene (PTFE).

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**Claim 34 (new):** An integrated circuit structure, comprising:

at least two metal interconnect lines;

a liner comprising silicon oxy-carbide located on and between said metal interconnect lines; and

a dielectric layer positioned between said metal interconnect lines, the liner positioned between at least a portion of the dielectric layer and the metal interconnect lines.

**Claim 35 (new):** The integrated circuit structure of Claim 34, wherein the dielectric layer comprises an intralevel dielectric layer positioned between metal interconnect lines in a level of the integrated circuit structure.

**Claim 36 (new):** The integrated circuit structure of Claim 34, wherein the dielectric layer comprises an interlevel dielectric layer positioned between conductive elements in different levels of the integrated circuit structure.

**Claim 37 (new):** The integrated circuit structure of Claim 34, wherein the dielectric layer comprises a fluorinated dielectric material.

**Claim 38 (new):** The integrated circuit structure of Claim 34, wherein the dielectric layer comprises polytetrafluoroethylene (PTFE).